

LISTING OF CLAIMS:

The following listing of claims replaces all previous versions and listings in the present application.

1. (Currently amended) An oscillator circuit comprising:

a CR circuit for providing a feedback circuit to an active device, wherein the CR circuit comprises a first resistor group and a capacitor; and

a second resistor group ~~comprises~~comprising one or more resistors, wherein the second resistor group adjusts a charge/discharge trigger voltage and a charge/discharge time associated with the capacitor of the CR circuit, wherein the second resistor group has a positive temperature coefficient that is larger than a positive temperature coefficient associated with the first resistor group.

2. (Original) The oscillator circuit of claim 1, wherein the first resistor group and the second resistor group are semiconductor resistor elements.

3. (Original) The oscillator circuit of claim 2, wherein the temperature coefficients of the first resistor group and the second resistor group are varied by changing an impurity density of the semiconductor resistor elements.

4. (Previously presented) The oscillator circuit of claim 2, wherein the semiconductor resistor elements are composed of one of an impurity doped polysilicon resistor and a diffused resistor.

5. (Original) The oscillator circuit of claim 1, wherein the oscillator circuit is integrated in one chip.

6. – 15. (Canceled)

16. (Currently amended) An oscillator circuit comprising:

a plurality of inverters connected in series;

a first resistor connected between an input terminal of a first inverter of the plurality of inverters and an output terminal of an odd number inverter of the plurality of inverters; and

a second resistor connected to the input terminal of the first inverter and to an output terminal of an even numbered inverter of the plurality of inverters through a capacitor, the second resistor adjusting a charge/discharge trigger voltage and a charge/discharge time associated with the capacitor, the second resistor having a positive temperature coefficient that is larger than a positive temperature coefficient associated with the first resistor.

17. (New) The oscillator circuit of claim 1, wherein the active device includes at least one inverter.

18. (New) The oscillator circuit of claim 1, wherein the active device includes three or more inverters connected in series.

19. (New) The oscillator circuit of claim 1, wherein:

the first resistor group includes one or more impurity doped polysilicon resistors;

and

the one or more resistors of the second resistor group include one or more p⁺-type diffused resistors.

20. (New) The oscillator circuit of claim 1, wherein:

the first resistor group includes at least one impurity doped polysilicon resistor;

and

the one or more resistors of the second resistor group include one or more p-type well diffused resistors.

21. (New) The oscillator circuit of claim 1, wherein:

the first resistor group includes at least one p⁺-type diffused resistor; and

the one or more resistors of the second resistor group include one or more p-type well diffused resistors.

22. (New) The oscillator circuit of claim 1, wherein:

the first resistor group includes at least one p⁺-type diffused resistor; and

the one or more resistors of the second resistor group include one or more n-type well diffused resistors.